

**PATENT ABSTRACTS OF JAPAN**(11)Publication number : **2004-238655**(43)Date of publication of application : **26.08.2004**

---

(51)Int.Cl. **C22C 5/06**  
**C23C 14/34**

---

(21)Application number : **2003-027101**(71)Applicant : **DEPT CORP**(22)Date of filing : **04.02.2003**(72)Inventor : **UENO TAKASHI**

---

**(54) SPUTTERING TARGET MATERIAL FOR FORMING THIN FILM, THIN FILM, ELECTRODE-WIRED LAYER, OPTICAL RECORDING MEDIUM, ELECTRONIC COMPONENT, OPTOELECTRONIC COMPONENT AND ELECTRONIC DEVICE**

**(57)Abstract:**

**PROBLEM TO BE SOLVED:** To provide a sputtering target material for forming a thin film, which improves manufacturing easiness in a step of manufacturing an alloy, and stability and simplicity in a sputtering step when using it for a sputtering target.

**SOLUTION:** The sputtering target material for forming the thin film is made of a metallic material including Ag as a main component and 0.1-3.0 wt.% Mo. The use of such a sputtering target material for forming the thin film solves the problems in a prior art, and realizes a technology having various superior characteristics as the components of the various electronic components, electronic devices, optoelectronic components and optical recording media, while utilizing the advantages of Ag.

---

**LEGAL STATUS**

[Date of request for examination] 19.12.2005

[Date of sending the examiner's decision of rejection]

[Kind of final disposal of application other than the examiner's decision of rejection or application converted registration]

[Date of final disposal for application]

[Patent number]

[Date of registration]

[Number of appeal against examiner's decision of rejection]

[Date of requesting appeal against examiner's decision of rejection]

[Date of extinction of right]

Copyright (C); 1998,2003 Japan Patent Office